

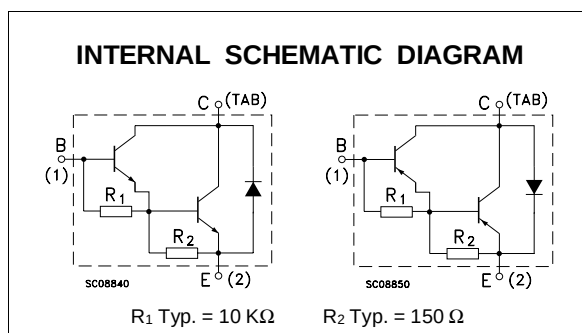
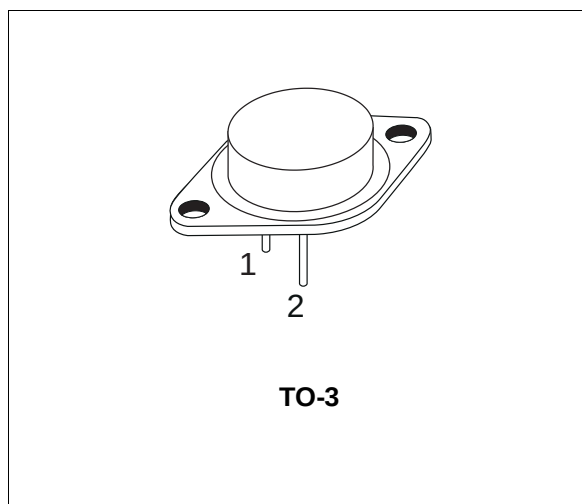
COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

■ SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The MJ2501 is a silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case. They are intended for use in power linear and switching applications.

The complementary NPN type is the MJ3001.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		PNP	MJ2501	
		NPN	MJ3001	
V _{CBO}	Collector-base Voltage (I _E = 0)		80	V
V _{CEO}	Collector-emitter Voltage (I _B = 0)		80	V
V _{EBO}	Emitter-base Voltage (I _C = 0)		5	V
I _C	Collector Current		10	A
I _B	Base Current		0.2	A
P _{tot}	Total Dissipation at T _c ≤ 25 °C		150	W
T _{stg}	Storage Temperature		-65 to 200	°C
T _j	Max. Operating Junction Temperature		200	°C

For PNP types voltage and current values are negative.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.17	°C/W
-----------------------	----------------------------------	-----	------	------

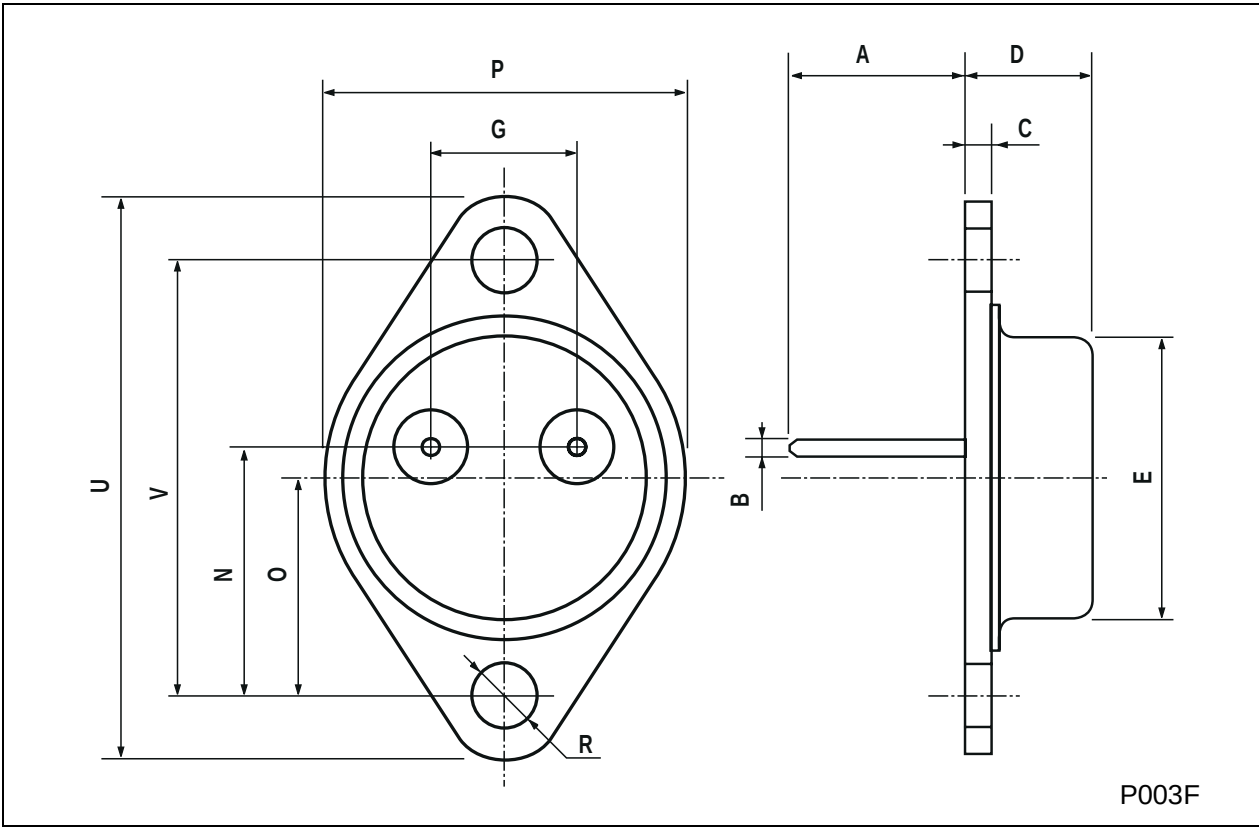
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CER}	Collector Cut-off Current (R _{BE} = 1 KΩ)	V _{CE} = 80 V T _{case} = 150 °C V _{CE} = 80 V			1 5	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V V _{CE} = 40 V			1 1	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	80			V
V _{CE(sat)} *	Collector-emitter Saturation Voltage	I _C = 5 A I _C = 10 A			2 4	V V
V _{BE} *	Base-emitter Voltage	I _C = 5 A V _{CE} = 3 V			3	V
h _{FE} *	DC Current Gain	I _C = 5 A V _{CE} = 3 V	1000			

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
For PNP types voltage and current values are negative.

TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A
...